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į [L Number	Hits	Search Text	DB	Time stamp
	1	20986	plasma and etching and heating and (wafer or semiconductor)	USPAT; US-PGPUB; EPO; JPO;	2004/08/17 12:56
	2	1663	wafer and boat and (batch or plurality adj4 wafers)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 12:57
	4	16986	microwave with heating	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 12:58
	5	441	<pre>(plasma and etching and heating and (wafer or semiconductor)) and (microwave with heating)</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17
	6	0	oscillat\$ and polar adj molocules	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:02
	7	0	polar adj molocules	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:03
	8	1621	dipoles and oscill\$	IBM TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:03
	9	463	microwave\$ and (dipoles and oscill\$)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:04
	11	0	(wafer and boat and (batch or plurality adj4 wafers)) and (microwave\$ and (dipoles and oscill\$))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:04
	10	8	(plasma and etching and heating and (wafer or semiconductor)) and (microwave\$ and (dipoles and oscill\$))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:19
	12	2865	DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:49
	14	3	(DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) adj5 microwave	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:30
	13	6	(DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) with microwave	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:30
	15	4	(DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) adj7 microwave	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:46
	16	9756	cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17
	17	74	(removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:48
	18	175	(removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/08/17
L				IBM_TDB	<u> </u>

. 19	9843	(cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17 13:48
20	47	((cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))) with microwave	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17 13:49
21	14985	heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:49
22	108	heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:50
23	152	(((cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))) with microwave) or (heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17 13:50
24	30949	after adj2 etching	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:50
25	0	(after adj2 etching) with ((((cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))) with microwave) or (heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17
26	3651	<pre>(plasma and etching and heating and (wafer or semiconductor)) and (after adj2 etching)</pre>	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:51
27	58	(plasma and etching and heating and (wafer or semiconductor)) and ((((cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))) with microwave) or (heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17 14:11
28	7	(heating with microwave) with plasma adj chamber	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:53
29	17	(heating with microwave) with plasma adj (vessel or reactor or chamber)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:54
30	0	(heating with microwave) adj4 (plasma adj (vessel or reactor or chamber))	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:54
31	0	(heating with microwave) adj7 (plasma adj (vessel or reactor or chamber))	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:54
32	17	((heating with microwave) with plasma adj chamber) or ((heating with microwave) with plasma adj (vessel or reactor or chamber))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17 13:55

33	152	((plasma and etching and heating and	USPAT;	2004/08/17
		(wafer or semiconductor)) and	US-PGPUB;	14:12
		((((cleaning ADJ5 (WAFER OR SEMICONDUCTOR	EPO; JPO;	
		OR CHIP)) or ((removing adj residue) ADJ5	IBM TDB	
		(WAFER OR SEMICONDUCTOR OR CHIP)) or	_	
		((removing adj contaminants) ADJ5 (WAFER		
		OR SEMICONDUCTOR OR CHIP))) with		
		microwave) or (heating ADJ5 (WAFER OR		
		SEMICONDUCTOR OR CHIP) with microwave)))		
		or ((((cleaning ADJ5 (WAFER OR		
		SEMICONDUCTOR OR CHIP)) or ((removing adj		
		residue) ADJ5 (WAFER OR SEMICONDUCTOR OR		
		CHIP)) or ((removing adj contaminants)		
		ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)))		
		with microwave) or (heating ADJ5 (WAFER		
		OR SEMICONDUCTOR OR CHIP) with		
		microwave))		
34	1	(after adj2 etching) with (heating adj4	USPAT;	2004/08/17
		microwave)	US-PGPUB;	14:14
			EPO; JPO;	
			IBM_TDB	
35	71124	purging or evacuating	USPAT;	2004/08/17
			US-PGPUB;	14:14
			EPO; JPO;	
			IBM_TDB	
37	71142	(purging or evacuating) or ((((cleaning	USPAT;	2004/08/17
		ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or	US-PGPUB;	14:15
		((removing adj residue) ADJ5 (WAFER OR	EPO; JPO;	
		SEMICONDUCTOR OR CHIP)) or ((removing adj	IBM_TDB	
		contaminants) ADJ5 (WAFER OR		
		SEMICONDUCTOR OR CHIP))) with microwave)		
		or (heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave)) with (heating		
		adj4 microwave))		
38	0	(purging or evacuating) and ((((cleaning	USPAT;	2004/08/17
30		ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or	US-PGPUB;	14:15
		((removing adj residue) ADJ5 (WAFER OR	EPO; JPO;	1110
		SEMICONDUCTOR OR CHIP)) or ((removing adj	IBM TDB	
		contaminants) ADJ5 (WAFER OR		
		SEMICONDUCTOR OR CHIP))) with microwave)		
		or (heating ADJ5 (WAFER OR SEMICONDUCTOR		
		OR CHIP) with microwave)) with (heating		
1		adj4 microwave))		
36	18	((((cleaning ADJ5 (WAFER OR SEMICONDUCTOR	USPAT;	2004/08/17
		OR CHIP)) or ((removing adj residue) ADJ5	US-PGPUB;	14:15
		(WAFER OR SEMICONDUCTOR OR CHIP)) or	EPO; JPO;	
		((removing adj contaminants) ADJ5 (WAFER	IBM_TDB	
		OR SEMICONDUCTOR OR CHIP))) with		
		microwave) or (heating ADJ5 (WAFER OR		
		SEMICONDUCTOR OR CHIP) with microwave))	-	
		with (heating adj4 microwave)		